

ASMEX.328A



PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

7-18-02

Applicant : Michael A. Todd

Appl. No. : 10/074,633

Filed : February 11, 2002

For : DEPOSITION OVER MIXED
SUBSTRATES (as amended)

Examiner : Unknown

) Group Art Unit Unknown

) I hereby certify that this correspondence and
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) P.O. Box 2327, Arlington, VA 22202, on

4/9/02

(Date)

Joseph J. Mallon, Reg. No. 39,287

PRELIMINARY AMENDMENT

United States Patent and Trademark Office
P.O. Box 2327
Arlington, VA 22202

Dear Sir:

Prior to examination, please amend the above-referenced application as follows:

IN THE TITLE:

Please amend the title to read as follows:

DEPOSITION OVER MIXED SUBSTRATES

IN THE ABSTRACT:

Please replace the Abstract with the following new Abstract:

Chemical vapor deposition methods are used to deposit silicon-containing films over mixed substrates. Such methods are useful in semiconductor manufacturing to provide a variety of advantages, including uniform deposition over heterogeneous surfaces, high deposition rates, and higher manufacturing productivity. An example is in forming the base region of a heterojunction bipolar transistor, including simultaneous deposition over both single crystal semiconductor surfaces and amorphous insulating regions.